TO-92LM NPN Silicon NPN transistor in a TO-92LM Plastic Package.

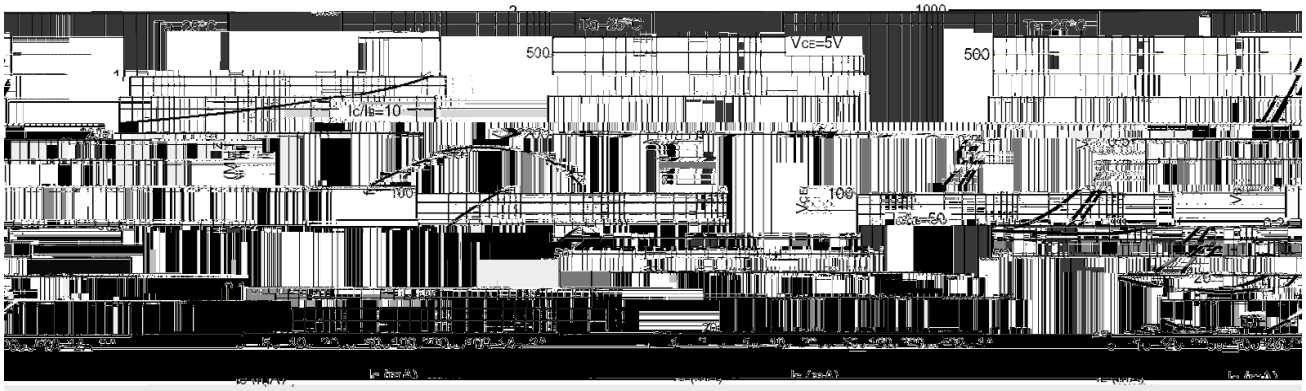
, 2SB1240

Low V

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	32	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	2.0	A
Collector Current (Pulse)	I_{CP}	2.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=50μA I_B=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	32			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=50μA I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V I_E=0			1.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE}=3.0V I_C=0.5A	120		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2.0A I_B=0.2A		0.5	0.8	V
Transition Frequency	f_T	V_{CE}=5.0V I_C=50mA f=100MHz		100		MHz
Collector output capac4fance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		30		pF

VCE(sat) – Ic

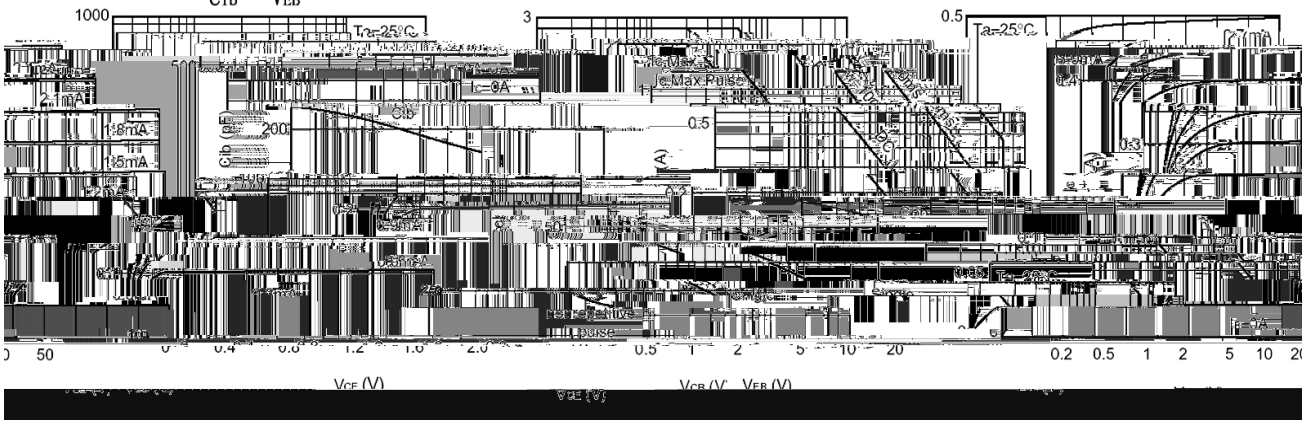


VBE(sat) – Ic

fT – IE

Cob – VCB

Cib – VEB

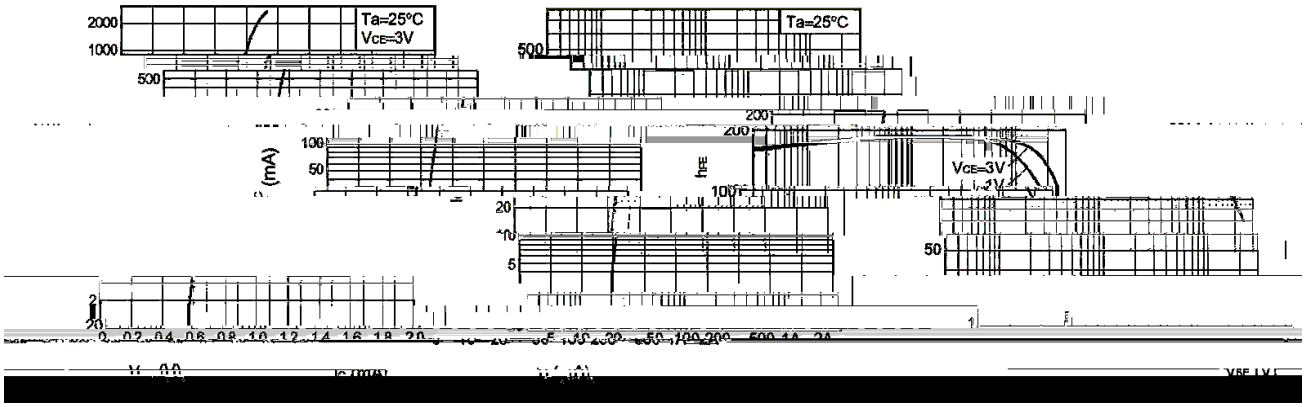


Ic – VCE

Ic – VCE

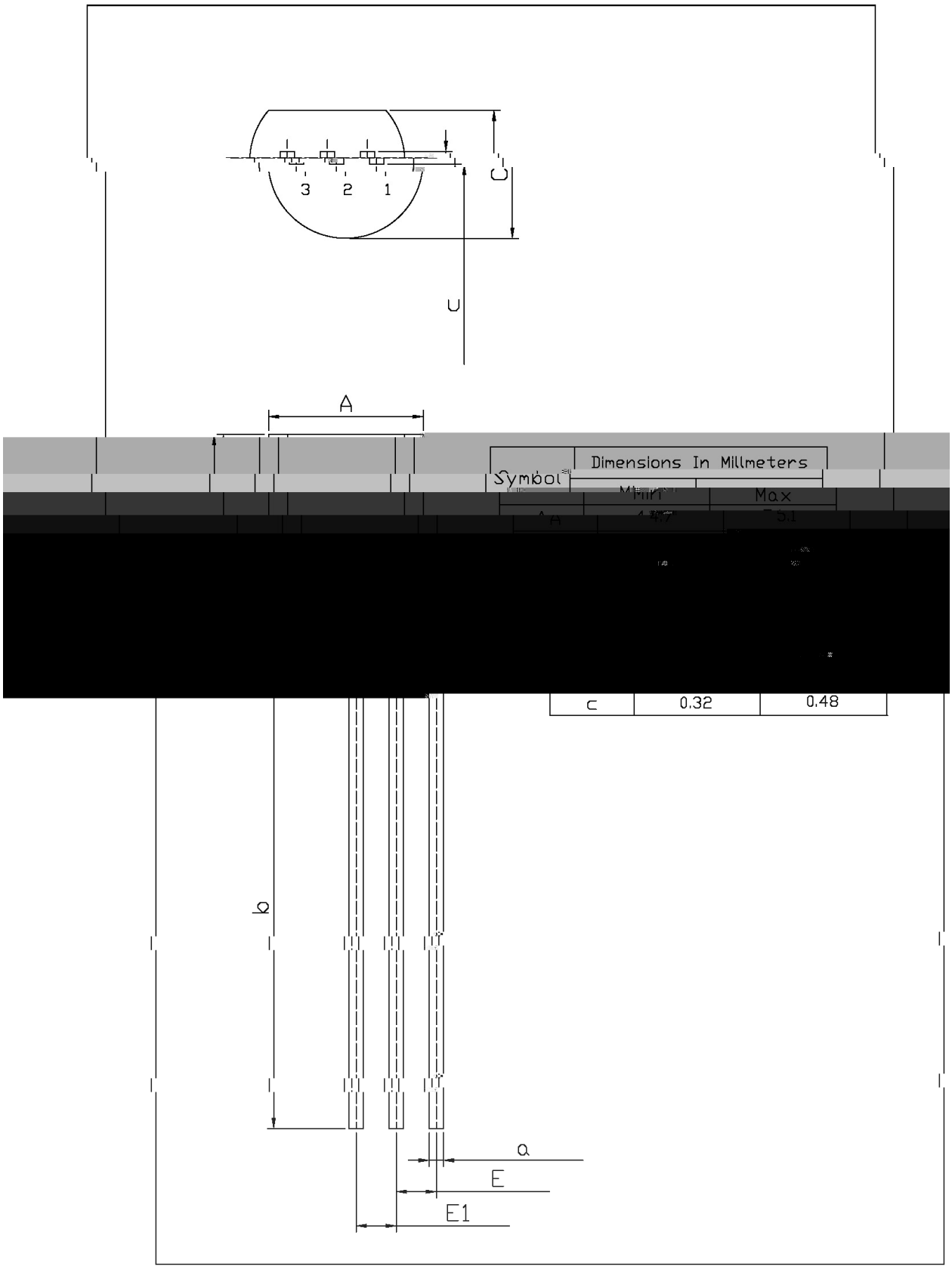
Ic – VBE

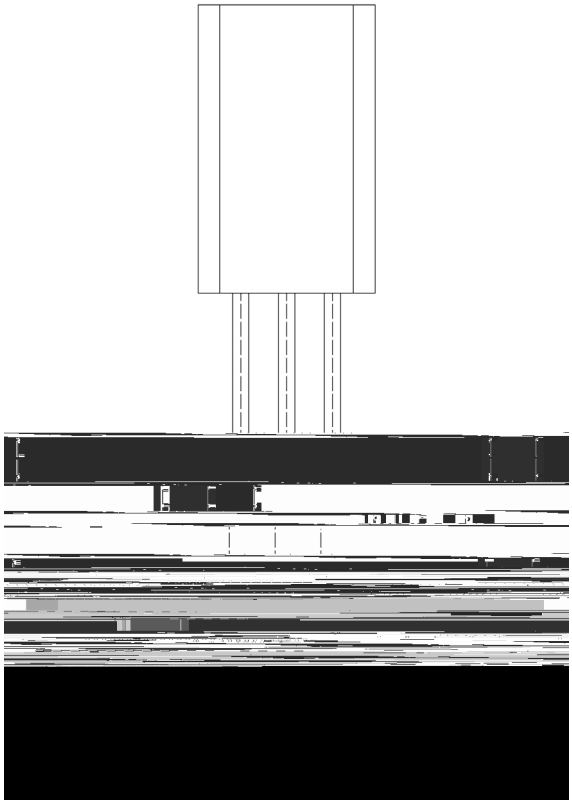
hFE – Ic

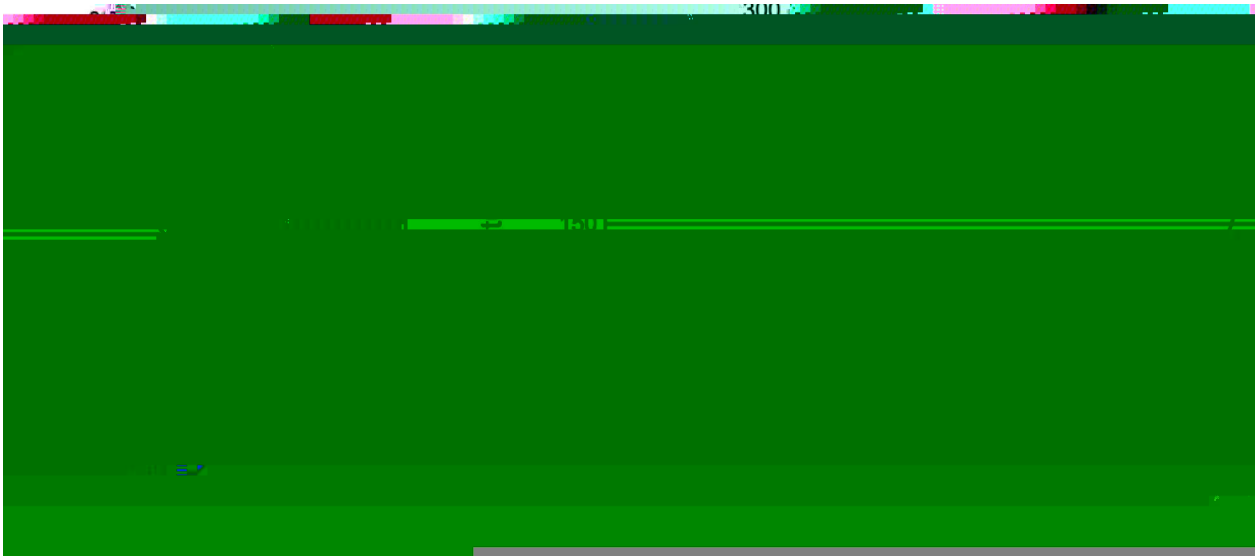


TO-92LM

Unit: mm







	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

270±5 10±1 sec.	Temp.:270±5